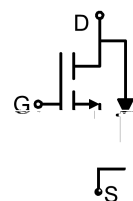


$V_{DSS}$	-20V
$R_{DS(on)}$	21.3m (typ.)
$I_D$	-6A



Advanced MOSFET process technology  
 Special designed for PWM, load switching and  
 general purpose applications  
 Ultra low on-resistance with low gate charge  
 Fast switching and reverse body recovery  
 150 operating temperature



It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-6	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-4	
$I_{DM}$	Pulsed Drain Current	-24	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	1.6	W
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$



$R_{JA}$	Junction-to-ambient ( )	—	75	/W
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@T<sub>A</sub>=25 unless otherwise specified

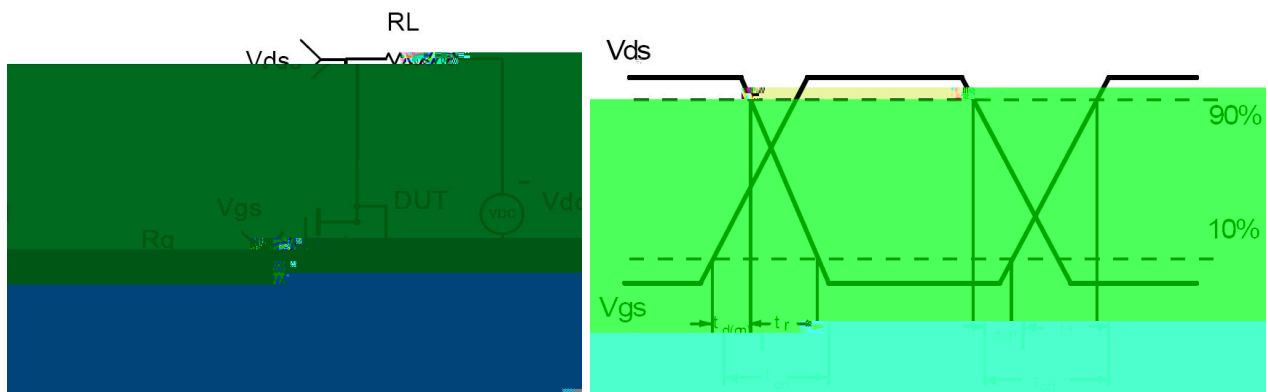
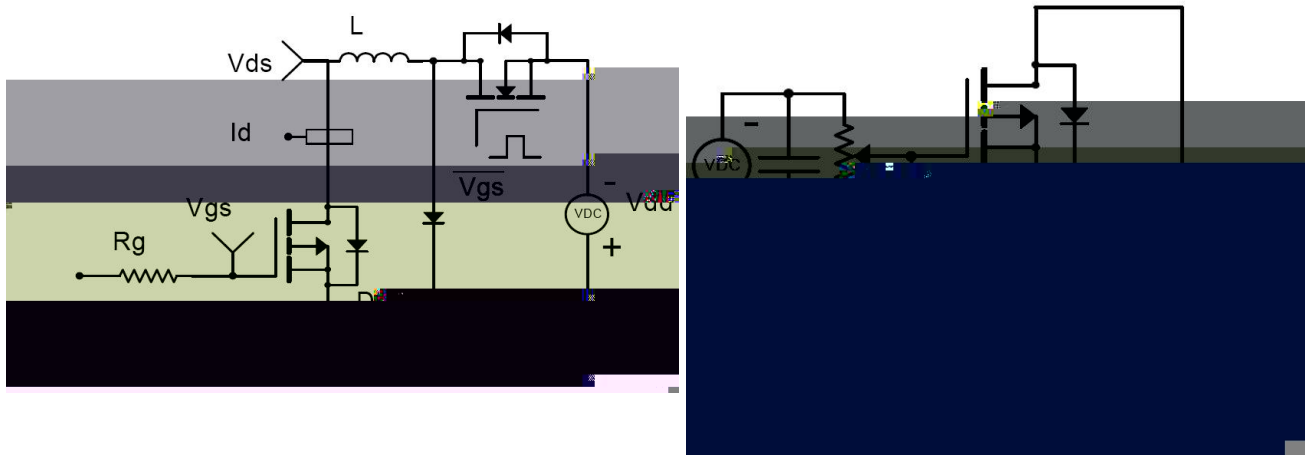
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	21.3	28	m	$V_{GS} = -4.5V, I_D = -5A$
		—	27.3	36	m	$V_{GS} = -2.5V, I_D = -4A$
$V_{GS(th)}$	Gate threshold voltage	-0.5	—	-1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$I_{DSS}$	Drain-to-Source leakage current	—	—	-1		

\*X'OMH-M-

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Best Buy \$v

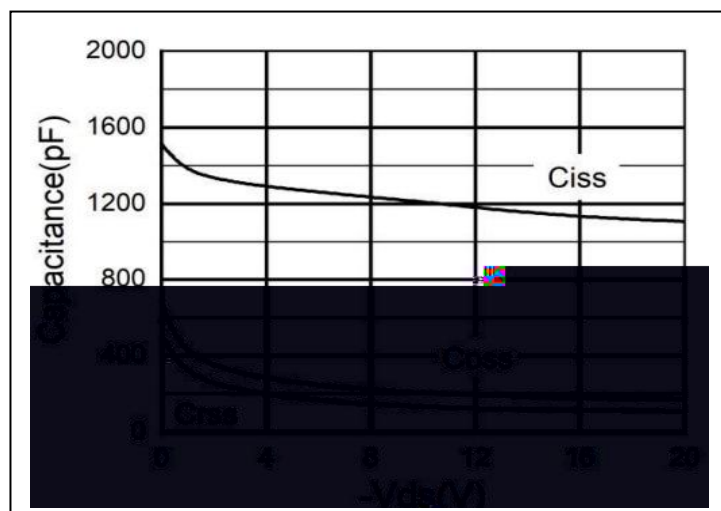
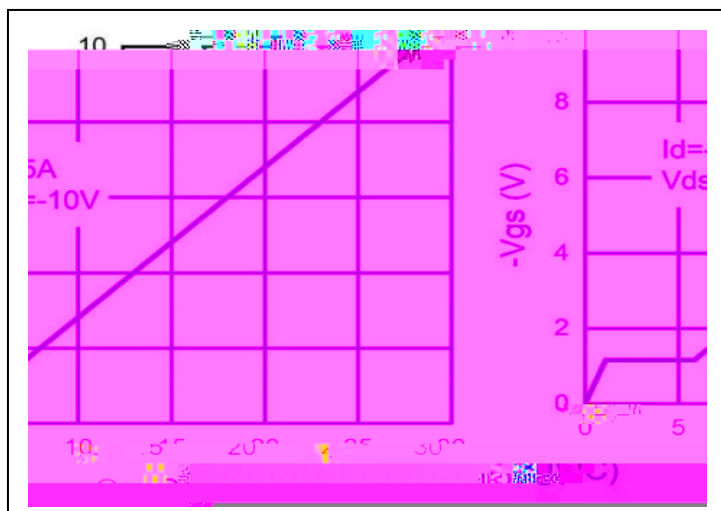
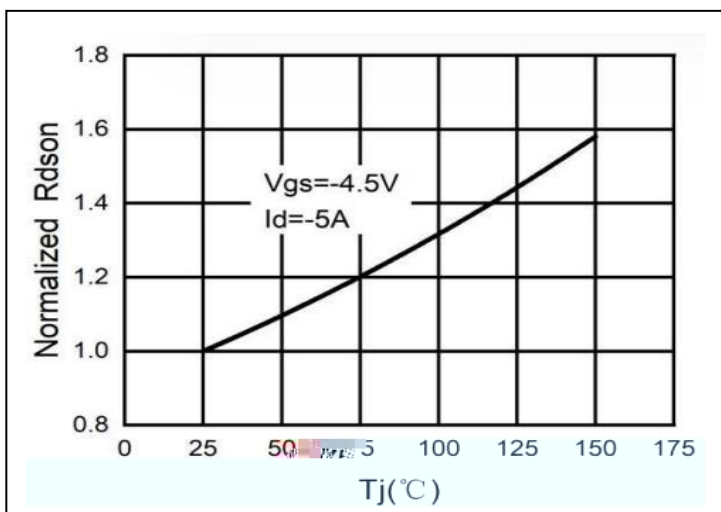
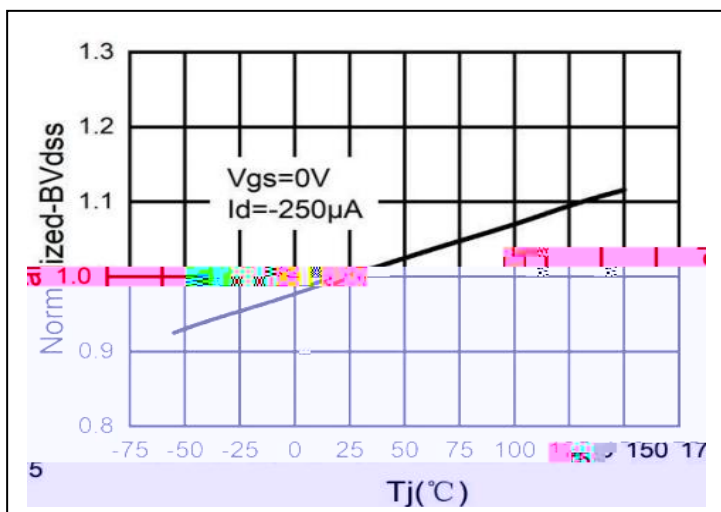
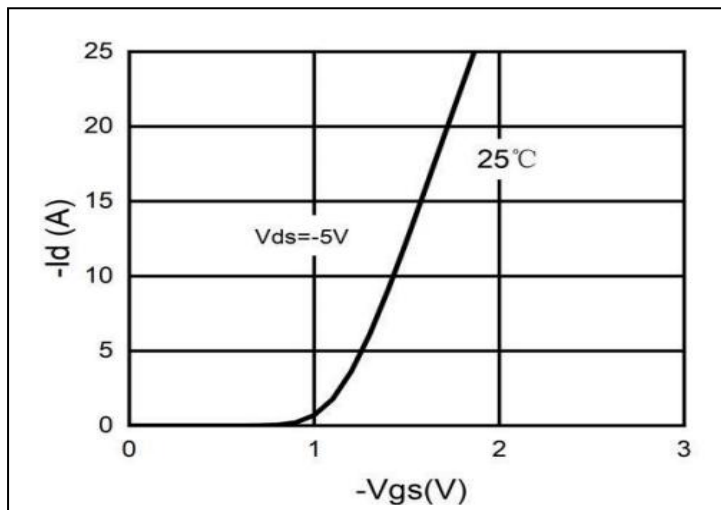
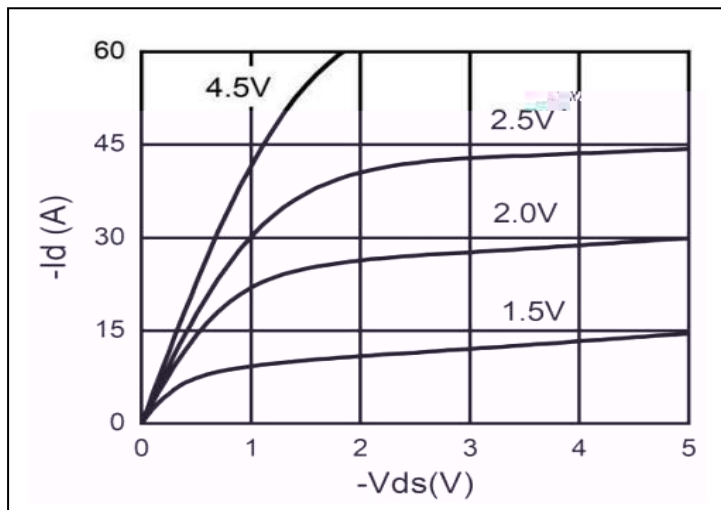


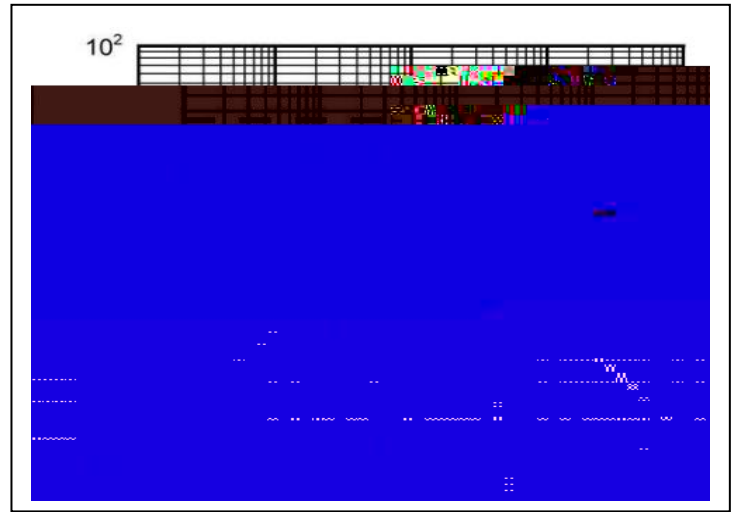
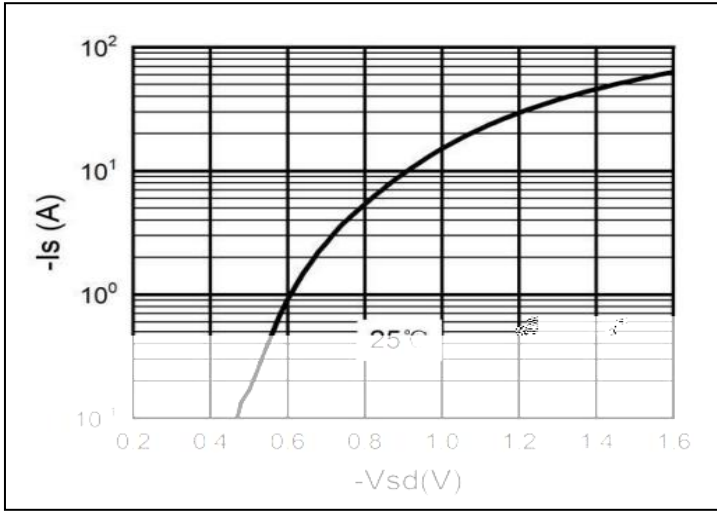
Calculated continuous current based on maximum allowable junction temperature.

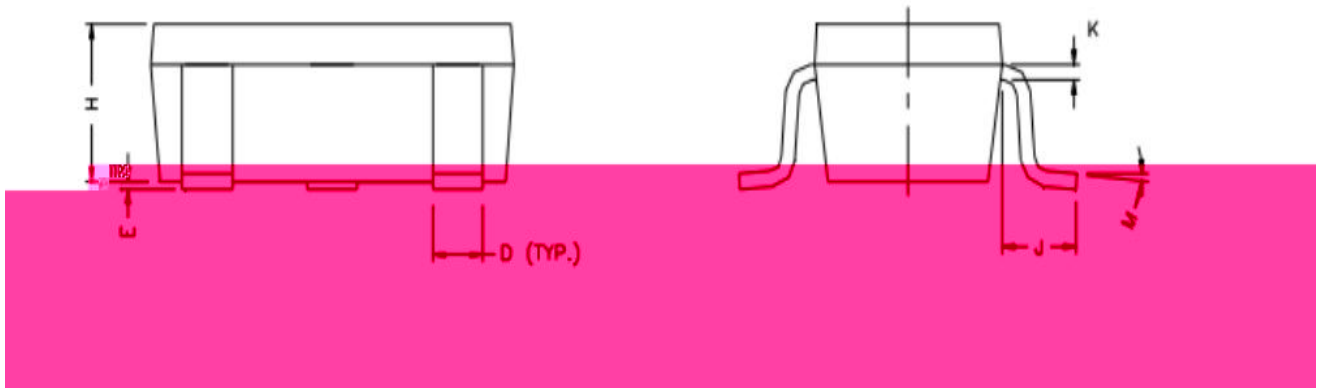
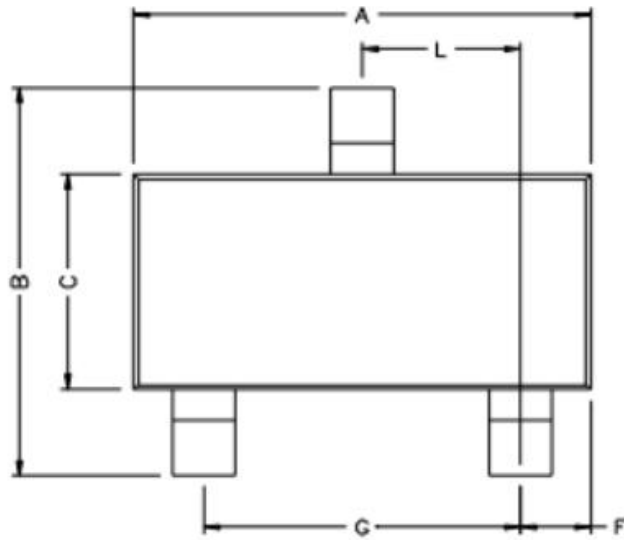
Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

The value of  $R_{JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$







REF.	Millimeter		REF.	Millimete	
	Min	Max		Min	Max
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°



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